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Table of Contents

Technical Sessions A1L-A: WBG Characterization

Oct. 14, 2014 10:30 am – 11:45 am

Session chair: *John Hostetler*

4500 Volt Si/SiC Hybrid Module Qualification for Modern Megawatt Scale Wind Energy Inverters.....1

William Erdman, *Cinch LLC*

David Grider, *CREE Inc.*

Edward VanBrunt, *CREE Inc.*

Understanding the Limitations and Impact Factors of Wide Bandgap Devices' High Switching-Speed Capability in a Voltage Source Converter.....7

Zheyu Zhang, *University of Tennessee*

Fred Wang, *University of Tennessee*

Leon M. Tolbert, *University of Tennessee*

Benjamin J. Blalock, *University of Tennessee*

Daniel Costinett, *University of Tennessee*

The Development of a High-Voltage Power Device Evaluation Platform.....13

Lixing Fu, *Ohio State University*

Xuan Zhang, *Ohio State University*

He Li, *Ohio State University*

Xintong Lu, *Ohio State University*

Jin Wang, *Ohio State University*

Technical Sessions A1L-B: WBG Application Challenges

Oct. 14, 2014 10:30 am – 11:45 am

Session chairs: *Chingchi Chen and Jürgen Schuderer*

Packaging SiC Power Semiconductors - Challenges, Technologies and Strategies....18

Jürgen Schuderer, *ABB Corporate Research*

Umamaheswara Vemulapati, *ABB Corporate Research*

Felix Traub, *ABB Corporate Research*

The Opportunities and Challenges of Wide-Band-Gap Technologies for Automotive Applications (Presentation only)

Chingchi Chen, Ford Motor Company
Ming Su, Ford Motor Company

Application-Based Review of GaN HFETs.....24

Edward Jones, University of Tennessee
Fred Wang, University of Tennessee
Burak Ozpineci, Oak Ridge National Laboratory

Technical Sessions A2L-A: GaN Devices I

Oct. 14, 2014 1:30 pm – 3:10 pm

Session chair: *Gaudenzio Meneghesso*

Vertical GaN Electronic Devices on Bulk-GaN Substrates (Presentation only)

David Bour, Avogy
Hui Nie, Avogy
Quentin Diduck, Avogy
Ozgur Aktas, Avogy
Tom Prunty, Avogy
Andrew Edwards, Avogy
Gangfeng Ye, Avogy
Ming Zhang, Avogy
Isik Kizilyalli, Avogy

Advances in Reliability and Operation Space of High-voltage GaN Power Devices Grown on Si Substrates.....30

Yifeng Wu, Transphorm Incorporated
Jose Guerrero, Transphorm Incorporated
J. McKay, Transphorm Incorporated
Kurt Smith, Transphorm Incorporated

Application Specific Device Characterization and Datasheet Parameters for Commercial (600V) GaN-on-Si-Based Conversion Switches (Presentation only)

Tim McDonald, International Rectifier Corporation
Deepak Veerreddy, International Rectifier Corporation
Mohamed Imam, International Rectifier Corporation

Degradation Mechanisms of AlGaIn/GaN HEMTs on Sapphire, Si, and SiC Substrates under Proton Irradiation.....33

Andrew Koehler, U.S. Naval Research Laboratory
Travis Anderson, U.S. Naval Research Laboratory
Jennifer Hite, U.S. Naval Research Laboratory
Bradley Weaver, U.S. Naval Research Laboratory
Marko Tadjer, U.S. Naval Research Laboratory
Micheal Mastro, U.S. Naval Research Laboratory
Jordan Greenlee, U.S. Naval Research Laboratory
Petra Specht, University of California Berkeley
Matthew Porter, Naval Postgraduate School
Todd Weatherford, Naval Postgraduate School
Karl Hobart, Naval Research Laboratory
Fritz Kub, Naval Research Laboratory

Technical Sessions A2L-B: Power Module

Oct. 14, 2014 1:30 pm – 3:10 pm

Session chairs: *Laura Marlino and Alan Mantooth*

High-Temperature SiC Power Module with Integrated SiC Gate Drivers for Future High-Density Power Electronics Applications.....36

Bret Whitaker, Arkansas Power International, Inc.
Zach Cole, Arkansas Power International, Inc.
Brandon Passmore, Arkansas Power International, Inc.
Daniel Martin, Arkansas Power International, Inc.
Ty McNutt, Arkansas Power International, Inc.
Alex Lostetter, Arkansas Power International, Inc.
M. Nance Ericson, Oak Ridge National Laboratory
S. Shane Frank, Oak Ridge National Laboratory
Charles L. Britton, Oak Ridge National Laboratory
Laura D. Marlino, Oak Ridge National Laboratory
Alan Mantooth, University of Arkansas, Fayetteville
Matt Francis, University of Arkansas, Fayetteville
Ranjan Lamichhane, University of Arkansas, Fayetteville
Paul Shepherd, University of Arkansas, Fayetteville
Michael Glover, University of Arkansas, Fayetteville

Development of Packaging Technologies for Advanced SiC Power Modules.....42

Zhenxian Liang, Oak Ridge National Laboratory
Fred Wang, University of Tennessee
Leon M. Tolbert, University of Tennessee

<i>A 10-kW SiC Inverter with A Novel Printed Metal Power Module With Integrated Cooling Using Additive Manufacturing.....</i>	<i>48</i>
---	-----------

Madhu Chinthavali, Oak Ridge National Laboratory
Curt Ayers, Oak Ridge National Laboratory
Steven Campbell, Oak Ridge National Laboratory
Randy Wiles, Oak Ridge National Laboratory
Burak Ozpineci, Oak Ridge National Laboratory

<i>10 kV, 120 A SiC MOSFET Modules for a Power Electronics Building Block (PEBB).....</i>	<i>55</i>
---	-----------

Christina DiMarino, Virginia Polytechnic Institute and State University
Igor Cvetkovic, Virginia Polytechnic Institute and State University
Zhiyu Shen, Virginia Polytechnic Institute and State University
Rolando Burgos, Virginia Polytechnic Institute and State University
Dushan Boroyevich, Virginia Polytechnic Institute and State University

Technical Sessions A3L-A: GaN Devices II

Oct. 14, 2014 3:30 pm – 4:45 pm

Session chair: *Tim McDonald*

<i>Process Optimization of Multicycle Rapid Thermal Annealing of Mg-implanted GaN.....</i>	<i>59</i>
--	-----------

Jordan D. Greenlee, National Research Council
Boris N. Feigelson, Naval Research Laboratory
Travis J. Anderson, Naval Research Laboratory
Marko J. Tadjer, American Society for Engineering Education
Jennifer K. Hite, Naval Research Laboratory
Charles R. Eddy Jr., Naval Research Laboratory
Karl D. Hobart, Naval Research Laboratory
Francis J. Kub, Naval Research Laboratory

<i>Design and Fabrication of High Current AlGaIn/GaN HFET for Gen III Solid State Transformer.....</i>	<i>63</i>
--	-----------

In-Hwan Ji, NSF FREEDM Center at North Carolina State University
Sizhen Wang, NSF FREEDM Center at North Carolina State University
Bongmook Lee, NSF FREEDM Center at North Carolina State University
Haotao Ke, NSF FREEDM Center at North Carolina State University
Veena Misra, NSF FREEDM Center at North Carolina State University
Alex Q. Huang, NSF FREEDM Center at North Carolina State University

*Low ON-state Resistance of GaN PiN Rectifiers grown on FS-GaN Substrate
(Presentation only)*

Jeomoh Kim, Georgia Institute of Technology
Tsung-Ting Kao, Georgia Institute of Technology
Mi-hee Ji, Georgia Institute of Technology
Yi-Che Lee, Georgia Institute of Technology
Teeradetch Georgia Institute of Technology
Detchprohm, Georgia Institute of Technology
Russell Dupis, Georgia Institute of Technology
Shyh-Chiang Shen, Georgia Institute of Technology

Technical Sessions A3L-B: Gate Drive and Isolation Circuits

Oct. 14, 2014 3:30 pm – 4:45 pm

Session chairs: Jin Wang and Bulent Sarlioglu

An Integrated Gate Driver in 4H-SiC for Power Converter Applications.....66

M. Nance Ericson, Oak Ridge National Laboratory
S. Shane Frank, Oak Ridge National Laboratory
Charles L. Britton, Oak Ridge National Laboratory
Laura D. Marlino, Oak Ridge National Laboratory
Devon D. Janke, Oak Ridge National Laboratory
Dianne B. Ezell, Oak Ridge National Laboratory
Sei-Hyung Ryu, Cree Inc.
Ranjan Lamichhane, University of Arkansas
A. Matt Francis, University of Arkansas
Paul D. Shepherd, University of Arkansas
Michael D. Glover, University of Arkansas
H. Alan Mantooth, University of Arkansas
Bret Whitaker, Arkansas Power International, Inc.
Zach Cole, Arkansas Power International, Inc.
Brandon Passmore, Arkansas Power International, Inc.
Ty McNutt, Arkansas Power International, Inc.

*Understanding the Influence of Dead-time on GaN Based Synchronous Boost Converter
.....70*

Di Han, University of Wisconsin-Madison
Bulent Sarlioglu, University of Wisconsin-Madison

Discussions on the Semiconductor-based Galvanic Isolation.....75

Xuan Zhang, Ohio State University
Lixing Fu, Ohio State University
Mingzhi Leng, Ohio State University
Jin Wang, Ohio State University

Poster Sessions

Oct. 14, 2014 5:15 pm – 8:00 pm

Investigation of Driver Circuits for GaN HEMTs in Leaded Packages.....81

Zhan Wang, *Transphorm, Incorporated*
Jim Honea, *Transphorm, Incorporated*
Yuxiang Shi, *Florida State University*
Hui Li, *Florida State University*

An Isolated Bi-directional Soft-Switched High-Frequency-AC Link DC-AC Converter Using SiC MOSFETs.....88

Mengqi Wang, *North Carolina State University*
Suxuan Guo, *North Carolina State University*
Qingyun Huang, *North Carolina State University*
Wensong Yu, *North Carolina State University*
Alex Q.Huang, *North Carolina State University*

Dependence of Ti/C Ratio on Ohmic Contact with TiC Electrode in AlGaIn/GaN Structure.....94

Mari Okamoto, *Tokyo Institute of Technology*
Kuniyuki Kakushima, *Tokyo Institute of Technology*
Yoshinori Kataoka, *Tokyo Institute of Technology*
A. Nishiyama, *Tokyo Institute of Technology*
Nobuyuki Sugii, *Tokyo Institute of Technology*
Hitosh Wakabayashi, *Tokyo Institute of Technology*
Kazuo Tsutsui, *Tokyo Institute of Technology*
Hiroshi Iwai, *Tokyo Institute of Technology*
Wataru Saito, *Toshiba Corporation*

Impact of Current Measurement on Switching Characterization of GaN Transistors....98

Jennifer Lautner, *University of Erlangen-Nuremberg*
Bernhard Piepenbreier, *University of Erlangen-Nuremberg*

The Influence of SiC/SiO₂ Interface Morphology on the Electrical Characteristics of SiC MOS Structure.....103

Li Liu, *XiDian University*
Chunkun Jiao, *Auburn University*
Yi Xu, *Rutgers University*
Gang Liu, *Rutgers University*
Leonard Feldman, *Rutgers University*
Sarit Dhar, *Auburn University*

<i>Optically-Switched High-Voltage Bipolar SiC Device</i>	107
---	-----

Supid K. Mazumber, *University of Illinois-Chicago*
 Alireza Mojab, *University of Illinois-Chicago*
 Lin Cheng, *CREE Inc.*
 Anant Agarwal, *Department of Energy*
 Charles Scozzie, *U.S. Army Research Laboratory*

Technical Sessions B1L-A: Gate Dielectrics

Oct. 15, 2014 10:30 am – 11:45 am

Session chair: Sarit Dhar

<i>Enhanced Oxidation of SiC Substrates using La₂O₃ Capped Annealing and a Proposal for Uniform LaSiON Gate Dielectric Formation</i>	110
--	-----

Yiming Lei, *Tokyo Institute of Technology*
 Shu Munekiyo, *Tokyo Institute of Technology*
 Takamasa Kawanago, *Tokyo Institute of Technology*
 Kuniyuki Kakushima, *Tokyo Institute of Technology*
 Hitoshi Wakabayashi, *Tokyo Institute of Technology*
 Kazuo Tsutsui, *Tokyo Institute of Technology*
 Hiroshi Iwai, *Tokyo Institute of Technology*
 Masayuki Furuhashi, *Mitsubishi Electric Corporation*
 Naruhisa Miura, *Mitsubishi Electric Corporation*

<i>Passivation of SiO₂/SiC Interface with La₂O₃ Capped Oxidation</i>	114
---	-----

Shu Munekiyo, *Tokyo Institute of Technology*
 Yiming Lei, *Tokyo Institute of Technology*
 Kenji Natori, *Tokyo Institute of Technology*
 Hiroshi Iwai, *Tokyo Institute of Technology*
 Takamasa Kawanago, *Tokyo Institute of Technology*
 Kuniyuki Kakushima, *Tokyo Institute of Technology*
 K. Kataoka, *Tokyo Institute of Technology*
 A. Nishiyama, *Tokyo Institute of Technology*
 Nobuyuki Sugii, *Tokyo Institute of Technology*
 Hitoshi Wakabayashi, *Tokyo Institute of Technology*
 Kazuo Tsutsui, *Tokyo Institute of Technology*
 Masayuki Furuhashi, *Mitsubishi Electric Corporation*
 Naruhisa Miura, *Mitsubishi Electric Corporation*
 S. Yamakawa, *Mitsubishi Electric Corporation*

<i>Effect of Post Deposition Annealing for High Mobility 4H-SiC MOSFET Utilizing Lanthanum Silicate and Atomic Layer Deposited SiO₂</i>	117
--	-----

Xiangyu Yang, North Carolina State University
 Bongmook Lee, North Carolina State University
 Veena Misra, North Carolina State University

Technical Sessions B1L-B: High Efficiency Power Converters

Oct. 15, 2014 10:30 am – 11:45 am

Session chairs: *Robert Dean and Benjamin Blalock*

<i>Wide Band Gap Power Devices Based High Efficiency Power Converters for Data Center Application</i>	121
---	-----

Weimin Zhang, University of Tennessee
 Ben Guo, University of Tennessee
 Fan Xu, University of Tennessee
 Yutian Cui, University of Tennessee
 Yu Long, University of Tennessee
 Fred Wang, University of Tennessee
 Leon M. Tolbert, University of Tennessee
 Benjamin J. Blalock, University of Tennessee
 Daniel J. Costinett, University of Tennessee

<i>125 W Multiphase GaN/Si Hybrid Point of Load Converter for Improved High Load Efficiency</i>	127
---	-----

Luke L. Jenkins, Auburn University
 Benjamin K. Rhea, Auburn University
 William Abell, Auburn University
 Frank T. Werner, Auburn University
 Christopher G. Wilson, Auburn University
 Robert N. Dean, Auburn University
 Daniel K. Harris, Auburn University

<i>A Full-Bridge Current-Source Isolated DC/DC Converter with Reduced Number of Switches and Voltage Stresses for Photovoltaic Applications</i>	133
---	-----

Feng Guo, Ohio State University
 Lixing Fu, Ohio State University
 He Li, Ohio State University
 Mohammed Alsolami, Ohio State University
 Xuan Zhang, Ohio State University
 Jie Zhang, Hubei University of Technology
 Jin Wang, Ohio State University

Technical Sessions B2L-A: SiC II

Oct. 15, 2014 3:20 pm – 5:00 pm

Session chair: *Avinash Kashyap*

Reliability and Stability of SiC power MOSFETs and Next-Generation SiC MOSFETs.....139

Brett Hull, *Cree Incorporated*
Scott Allen, *Cree Incorporated*
Jon Zhang, *Cree Incorporated*
Don Gajewski, *Cree Incorporated*
Vipindas Pala, *Cree Incorporated*
Jim Richmond, *Cree Incorporated*
Sei-Hyung Ryu, *Cree Incorporated*
Michael O'Loughlin, *Cree Incorporated*
Edward VanBrunt, *Cree Incorporated*
Lin Cheng, *Cree Incorporated*
Al Burk, *Cree Incorporated*
Jeff Casady, *Cree Incorporated*
David Grider, *Cree Incorporated*
John Palmour, *Cree Incorporated*

6.5 kV Normally-off JFETs Technology Status.....143

John L. Hostetler, *United Silicon Carbide, Incorporated*
Petre Alexandrov, *United Silicon Carbide, Incorporated*
Xueqing Li, *United Silicon Carbide, Incorporated*
Leonid Fursin, *United Silicon Carbide, Incorporated*
Anup Bhalla, *United Silicon Carbide, Incorporated*

Silicon Carbide Transient Voltage Suppressor for Next Generation Lightning Protection.....147

Avinash Kashyap, *GE Global Research Center*
Peter Sandvik, *GE Global Research Center*
James McMahon, *GE Global Research Center*
Alexander Bolotnikov, *GE Global Research Center*
Jeffrey Erlbaum, *GE Global Research Center*
Emad Andarawis, *GE Global Research Center*

Temperature Dependent Design of Silicon Carbide Schottky Diodes.....151

Rahul Radhakrishnan, *Global Power Technologies Group*
Tony Witt, *Global Power Technologies Group*
Richard Woodin, *Global Power Technologies Group*

Technical Sessions B2L-B: GaN Power Converters

Oct. 15, 2014 3:20 pm – 5:00 pm

Session chairs: *Eric Persson and Kevin Bai*

*Matching GaN characteristics to power circuit topology maximizes performance benefit
(presentation only)*

Eric Persson, *International Rectifier Corporation*

A 12 to 1 V Five Phase Interleaving GaN POL Converter for High Current Low Voltage Applications.....155

Benjamin Rhea, *Auburn University*

Luke Jenkins, *Auburn University*

William Abell, *Auburn University*

Frank Werner, *Auburn University*

Christopher Wilson, *Auburn University*

Robert Dean, *Auburn University*

Daniel Harris, *Auburn University*

High-Frequency Wireless Charging System Study Based on Normally-off GaN HEMTs.....159

Yongsheng Fu, *Kettering University*

Lei Shi, *Kettering University*

Hua Bai, *Kettering University*

Reflected Wave Phenomenon in Motor Drive Systems Using Wide Bandgap Devices.....164

Mark Scott, *Ohio State University,*

Jared Brockman, *Ohio State University,*

Boxue Hu, *Ohio State University,*

Lixing Fu, *Ohio State University,*

Longya Xu, *Ohio State University,*

Jin Wang, *Ohio State University,*

Rachid Darbali Zamora, *University of Puerto Rico*

2014 WiPDA Tutorials

Oct. 13, 2014, 1:00 pm- 3:00 pm

Chair: Madhu Chinthavali

Driving and Characterization of Wide Bandgap Semiconductors for Voltage Source Converter Applications.....169

Fred Wang and Zheyu Zhang, *University of Tennessee*

Chair: Daniel Costinett

Reliability and High Field Related Issues in GaN-HEMT Devices.....211

Gaudenzio Meneghesso, University of Padova

Oct. 13, 2014, 3:30 pm- 5:30 pm

Chair: Madhu Chinthavali

WBG Devices Enabled MV Power Converters for Utility Applications – Opportunities and Challenges.....297

Ram Adapa, Electric Power Research Institute;

Subhashish Bhattacharya, North Carolina State University

Chair: Daniel Costinett

Packaging Technologies to Exploit the Attributes of WBG Power Electronics.....360

Zhenxian Liang